

NPN SILICON GERMANIUM RF TRANSISTOR NESG3031M05

NPN SiGE RF TRANSISTOR FOR LOW NOISE, HIGH-GAIN AMPLIFICATION FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M05, 2012 PKG)

FEATURES

- The device is an ideal choice for low noise, high-gain amplification
- ★ NF = 0.6 dB TYP., G_a = 16.0 dB TYP. @ VcE = 2 V, Ic = 6 mA, f = 2.4 GHz NF = 0.95 dB TYP., G_a = 10.0 dB TYP. @ VcE = 2 V, Ic = 6 mA, f = 5.2 GHz NF = 1.1 dB TYP., G_a = 9.5 dB TYP. @ VcE = 2 V, Ic = 6 mA, f = 5.8 GHz
 - Maximum stable power gain: MSG = 14.0 dB TYP. @ VcE = 3 V, Ic = 20 mA, f = 5.8 GHz
 - SiGe HBT technology (UHS3) adopted: fmax = 110 GHz
 - Flat-lead 4-pin thin-type super minimold (M05, 2012 PKG)

★ ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Supplying Form
NESG3031M05	NESG3031M05-A	Flat-lead 4-pin thin-type super minimold (M05, 2012 PKG)	50 pcs (Non reel)	8 mm wide embossed taping Pin 3 (Collector), Pin 4 (Emitter) face the
NESG3031M05-T1	NESG3031M05-T1-A	(Pb-Free)	3 kpcs/reel	perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office. Unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25$ °C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	Vсво	12.0	V
Collector to Emitter Voltage	Vceo	4.3	٧
Emitter to Base Voltage	VEBO	1.5	٧
Collector Current	lc	35	mA
Total Power Dissipation	P _{tot} Note	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	−65 to +150	°C

Note Mounted on 1.08 cm² × 1.0 mm (t) glass epoxy PWB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

ELECTRICAL CHARACTERISTICS (TA = +25°C)

	Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
	DC Characteristics						
	Collector Cut-off Current	Ісво	$V_{CB} = 5 \text{ V}, I_E = 0 \text{ mA}$	1	1	100	nA
	Emitter Cut-off Current	ІЕВО	V _{EB} = 1 V, I _C = 0 mA	1	1	100	nA
	DC Current Gain	hfe Note 1	$V_{CE} = 2 \text{ V}, \text{ Ic} = 6 \text{ mA}$	220	300	380	_
	RF Characteristics						
	Insertion Power Gain	S _{21e} ²	Vce = 3 V, Ic = 20 mA, f = 5.8 GHz	6.0	8.5	I	dB
*	Noise Figure (1)	NF	$\label{eq:Vce} \begin{split} &\text{Vce} = 2 \text{ V, Ic} = 6 \text{ mA, f} = 2.4 \text{ GHz}, \\ &\text{Zs} = Z_{\text{Sopt}}, \text{ ZL} = Z_{\text{Lopt}} \end{split}$	ı	0.6	ı	dB
	Noise Figure (2)	NF	$\label{eq:Vce} \begin{split} &V\text{CE} = 2 \text{ V, Ic} = 6 \text{ mA, f} = 5.2 \text{ GHz,} \\ &Z\text{S} = Z\text{Sopt, } Z\text{L} = Z\text{Lopt} \end{split}$	ı	0.95	ı	dB
	Noise Figure (3)	NF	$\label{eq:Vce} \begin{split} &\text{Vce} = 2 \text{ V, Ic} = 6 \text{ mA, f} = 5.8 \text{ GHz}, \\ &\text{Zs} = Z_{\text{Sopt}}, \text{ ZL} = Z_{\text{Lopt}} \end{split}$	ı	1.1	1.5	dB
*	Associated Gain (1)	Ga	$\begin{split} &V_{\text{CE}} = 2 \text{ V, Ic} = 6 \text{ mA, f} = 2.4 \text{ GHz}, \\ &Z_{\text{S}} = Z_{\text{Sopt}}, Z_{\text{L}} = Z_{\text{Lopt}} \end{split}$	1	16.0	-	dB
	Associated Gain (2)	Ga	$\begin{split} &V_{CE}=2~V,~I_{C}=6~mA,~f=5.2~GHz,\\ &Z_{S}=Z_{Sopt},~Z_{L}=Z_{Lopt} \end{split}$	-	10.0	-	dB
	Associated Gain (3)	Ga	$\label{eq:Vce} \begin{split} &\text{Vce} = 2 \text{ V, Ic} = 6 \text{ mA, f} = 5.8 \text{ GHz}, \\ &\text{Zs} = Z_{\text{Sopt}}, \text{ ZL} = Z_{\text{Lopt}} \end{split}$	7.5	9.5	-	dB
	Reverse Transfer Capacitance	Cre Note 2	Vcв = 2 V, IE = 0 mA, f = 1 MHz	_	0.15	0.25	pF
	Maximum Stable Power Gain	MSG ^{Note}	VcE = 3 V, Ic = 20 mA, f = 5.8 GHz	11.0	14.0	-	dB
	Gain 1 dB Compression Output Power	Po (1 dB)	$\begin{split} &V_{\text{CE}} = 3 \text{ V, Ic (set)} = 20 \text{ mA,} \\ &f = 5.8 \text{ GHz, Zs} = Z_{\text{Sopt, ZL}} = Z_{\text{Lopt}} \end{split}$	ı	13.0	ı	dBm
	3rd Order Intermodulation Distortion Output Intercept Point	OIP ₃	$\begin{split} \text{VCE} &= 3 \text{ V, Ic (set)} = 20 \text{ mA,} \\ \text{f} &= 5.8 \text{ GHz, Zs} = Z_{Sopt, ZL} = Z_{Lopt} \end{split}$	_	18.0	-	dBm

Notes 1. Pulse measurement: PW \leq 350 $\mu\text{s}, \text{ Duty Cycle} \leq$ 2%

2. Collector to base capacitance when the emitter grounded

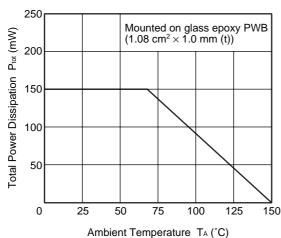
3. MSG =
$$\frac{S_{21}}{S_{12}}$$

hfe CLASSIFICATION

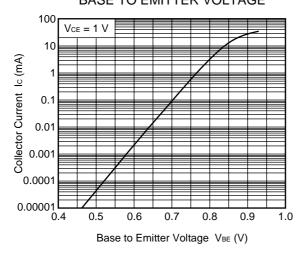
Rank	FB		
Marking	T1K		
h _{FE} Value	220 to 380		

TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

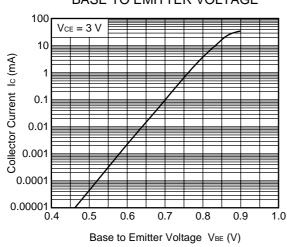




COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

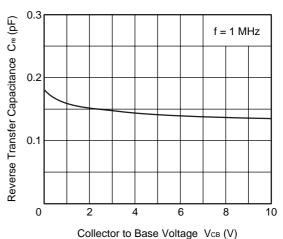


COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

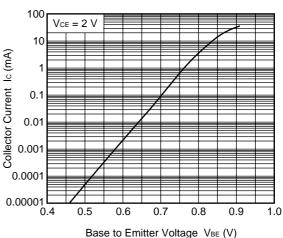


Remark The graphs indicate nominal characteristics.

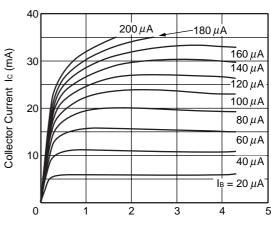
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



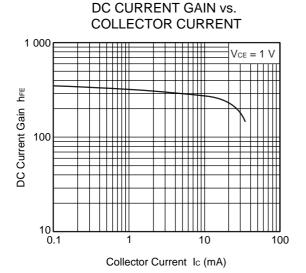
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

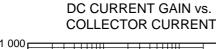


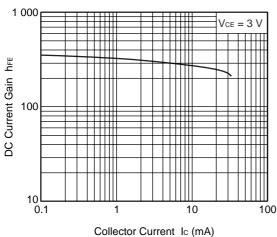
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



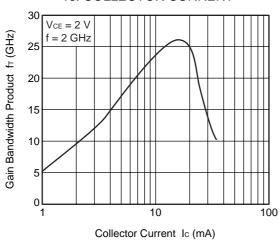
Collector to Emitter Voltage VcE (V)





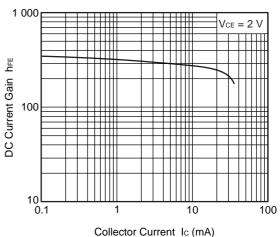


GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

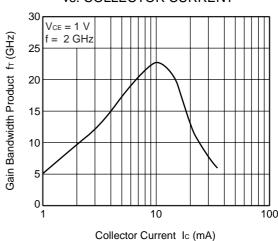


Remark The graphs indicate nominal characteristics.

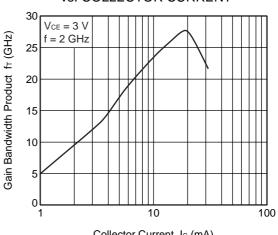


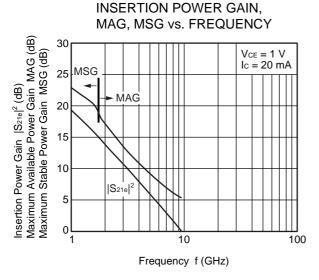


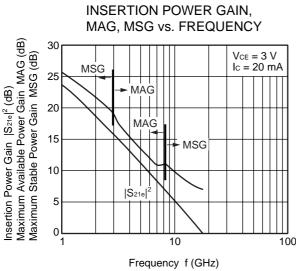
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

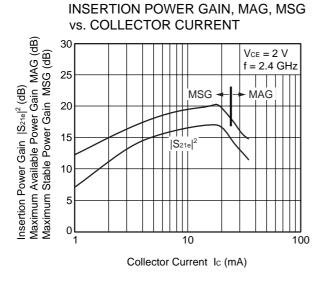


GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

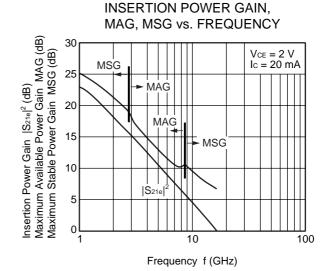


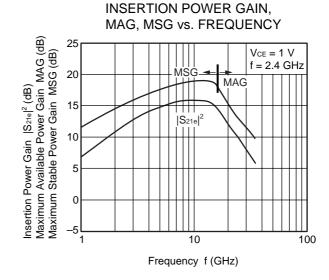


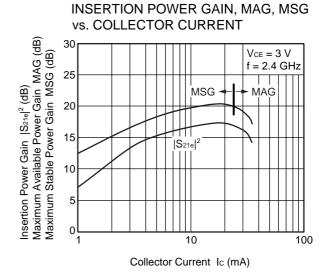




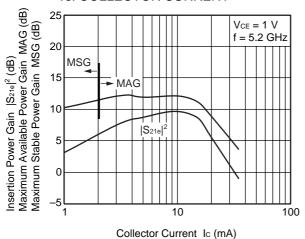




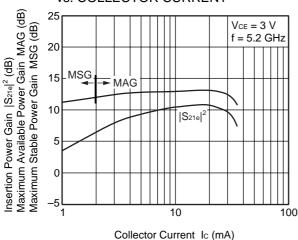




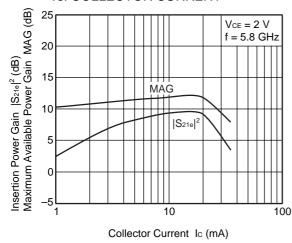
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

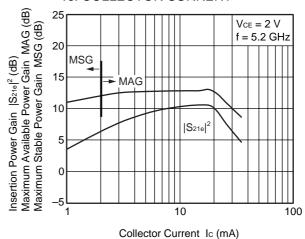


INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

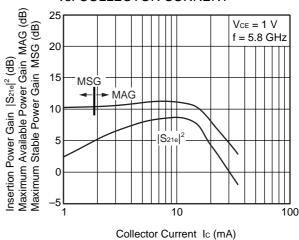


Remark The graphs indicate nominal characteristics.

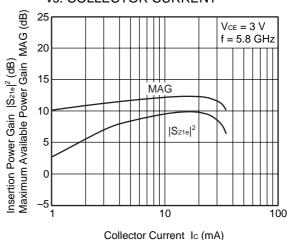
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

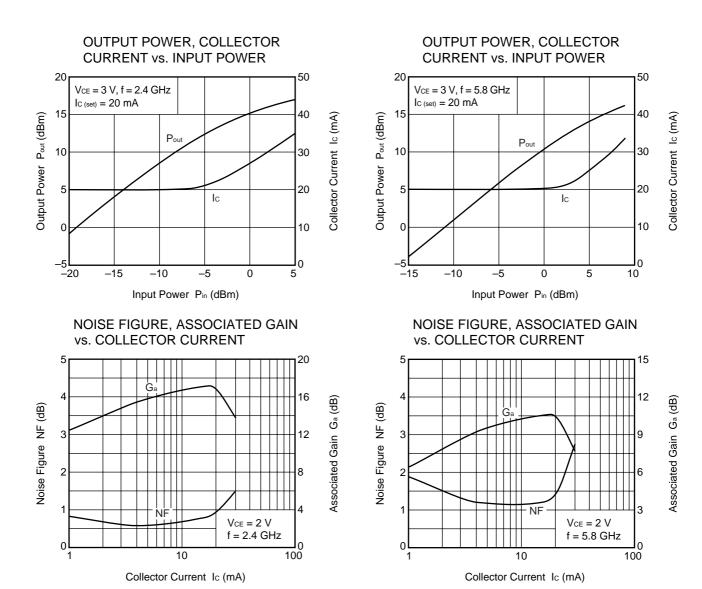


INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT

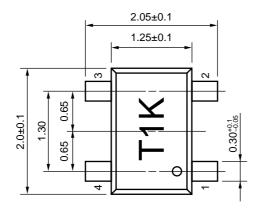


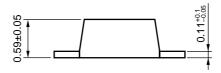


Remark The graphs indicate nominal characteristics.

PACKAGE DIMENSIONS

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M05, 2012 PKG) (UNIT: mm)





PIN CONNECTIONS

- 1. Base
- 2. Emitter
- 3. Collector
- 4. Emitter

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M8E 00.4-0110

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This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices		
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)	
Mercury	< 1000 PPM	Not Detected		
Cadmium	< 100 PPM	Not Detected		
Hexavalent Chromium	< 1000 PPM	Not Detected		
PBB	< 1000 PPM	Not Detected		
PBDE	< 1000 PPM	Not Detected		

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